

REMARKS

Claims 1, 3, and 5-23 are pending in this application. By this Amendment, claims 2 and 4 are canceled, claims 5 and 6 are amended because of the cancellation of claims 2 and 4, claims 1, 3, and 5-13 are amended for clarity and consistency, claims 1 and 3 are amended to more clearly distinguish over the applied references, and claims 21-23 are added. The amendments are supported in the specification by at least paragraphs [0010]-[0012], [0049], [0053], and [0058], and Fig. 1.

As discussed with Examiner Fenty by telephone on March 23, 2006, Applicant requests the opportunity to conduct a personal interview before the next action on the merits for this case. As requested, an Applicant Initiated Interview Request Form is attached.

The Office Action rejects claims 1-4, 7, 9-16 and 19 under 35 U.S.C. §102(b) over Yamazaki (U.S. Patent No. 5,858,823); claims 5, 6, 17, and 18 under 35 U.S.C. §103(a) over Yamazaki; and claims 8 and 20 under 35 U.S.C. §103(a) over Yamazaki in view of an article by Ishihara. The rejections are respectfully traversed.

With regard to independent claim 1, Yamazaki fails to disclose a complementary transistor circuit having a first transistor and a second transistor having different conductivity types, with a first channel region and a second channel region both formed in one single crystal grain.

The Office Action at page 3 asserts, with regard to claim 2, that Yamazaki discloses two transistors (and channel regions) formed in one single crystal grain because there allegedly is no grain boundary between single crystal grains 121 and 122. However, as shown in Yamazaki at Figs. 12A-12B, monodomain regions 121-123 are adjacent to each other through a grain boundary 100. See Yamazaki at col. 14, lines 9-11. Accordingly, the Office Action is incorrect in its interpretation of Yamazaki. Yamazaki does not disclose a first and second (or first and second channel region) transistor formed in one single crystal grain.

Furthermore, col. 4, lines 47-50, of Yamazaki (referred to at page 3 of the Office Action) does not disclose a first and second transistor formed in a single crystal grain, because that portion of Yamazaki refers to a single TFT formed in a single crystal region.

With regard to independent claim 14, Yamazaki fails to disclose a complementary thin film transistor circuit having a first-conductivity-type thin film transistor and a second-conductivity-type thin film transistor formed using same single crystal grains. As explained above, Yamazaki fails to disclose a first and second transistor formed in a single crystal grain.

For the foregoing reasons, Yamazaki, alone or in combination with the Ishihara article, fails to disclose all of the features recited in independent claims 1 and 14. It is respectfully requested that the rejections be withdrawn.

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



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JAO:SWA/jam

Attachments:

Request for Continued Examination
Amendment Transmittal
Applicant Initiated Interview Request Form

Date: March 28, 2006

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